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(54) **Title:** SEMICONDUCTOR SUBSTRATE POLISHING WITH POLISHING PAD TEMPERATURE CONTROL

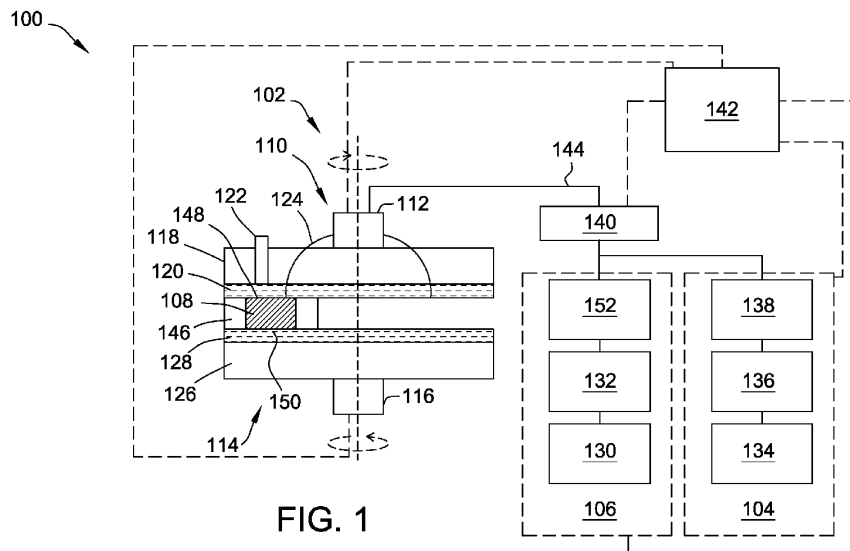


FIG. 1

(57) **Abstract:** A method of preheating a polishing pad of a semiconductor wafer polishing system includes heating a fluid to a first predetermined temperature. The method also includes applying the fluid to the polishing pad. The method further includes rotating the polishing pad such that the fluid covers the polishing pad. The fluid increases a polishing pad temperature to a second predetermined temperature.

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